

NPN Epitaxial Planar Transistor

BTC1510J3

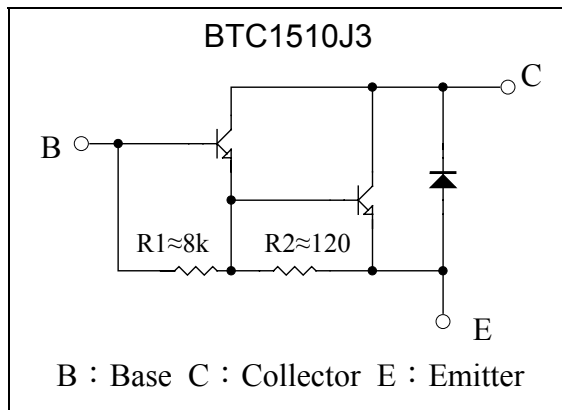
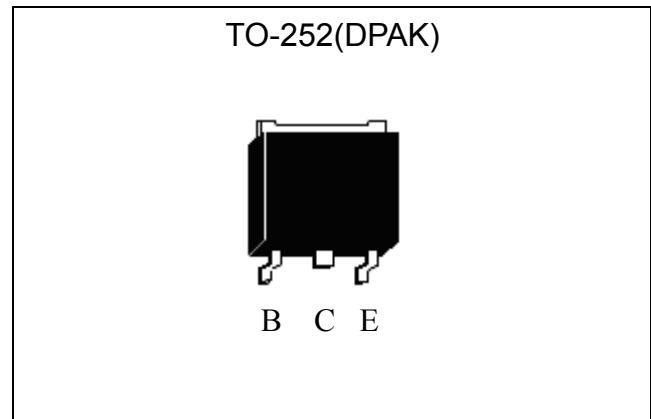
BV_{CEO}	150V
I_C	10A

Description

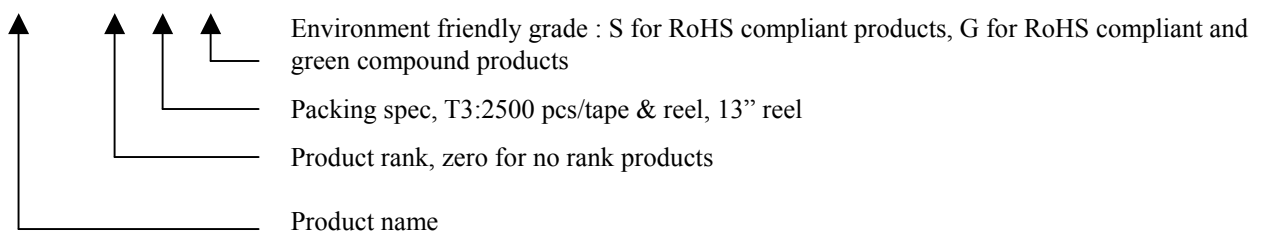
The BTC1510J3 is a NPN Darlington transistor, designed for general purpose amplifier and low speed switching application.

Features:

- High BV_{CEO}
- Low $V_{CE(SAT)}$
- High current gain
- Monolithic construction with built-in base-emitter shunt resistors
- TO-252 surface mount package
- RoHS compliant package

Equivalent Circuit

Outline

Ordering Information

Device	Package	Shipping
BTC1510J3-XX-T3-X	TO-252 (RoHS compliant package)	2500 pcs / Tape & Reel





Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-Base Voltage	V _{CB0}	150	V
Collector-Emitter Voltage	V _{CE0}	150	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _{C(DC)}	10	A
	I _{C(Pulse)}	15 *1	
Power Dissipation	Pd(T _A =25°C)	1.75	W
	Pd(T _C =25°C)	20	
Operating Junction Temperature Range	T _j	-55~+150	°C
Storage Temperature Range	T _{stg}	-55~+150	°C

Note : *1. Single Pulse Pw=100ms

Characteristics (Ta=25°C)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV _{CB0}	150	-	-	V	I _C =100μA, I _E =0
BV _{CE0}	150	-	-	V	I _C =1mA, I _B =0
I _{CE0}	-	-	200	μA	V _{CE} =150V, I _E =0
I _{CB0}	-	-	200	μA	V _{CB} =150V, I _E =0
I _{EBO}	-	-	2	mA	V _{EB} =5V, I _C =0
*V _{CE(sat) 1}	-	-	1.5	V	I _C =5A, I _B =10mA
*V _{CE(sat) 2}	-	-	3	V	I _C =10A, I _B =100mA
*V _{CE(sat) 3}	-	-	2	V	I _C =5A, I _B =2.5mA
*V _{BE(sat)}	-	-	2	V	I _C =5A, I _B =5mA
*V _{BE(on) 1}	-	-	2.8	V	V _{CE} =3V, I _C =5A
*V _{BE(on) 2}	-	-	4.5	V	V _{CE} =3V, I _C =10A
*V _{FEC}	-	-	3	V	I _C =5A
*h _{FE1}	2	-	20	K	V _{CE} =3V, I _C =5A
*h _{FE2}	100	-	-	-	V _{CE} =3V, I _C =10A

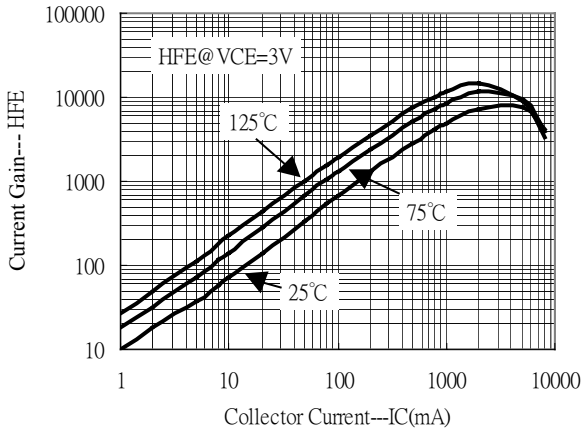
*Pulse Test : Pulse Width ≤380μs, Duty Cycle≤2%

Classification Of V_{CE(sat) 1}

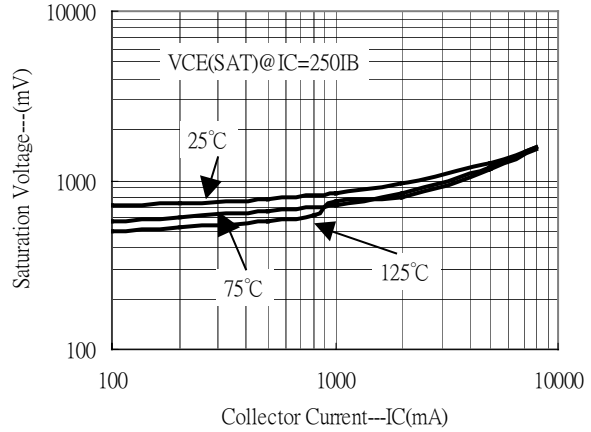
Rank	KA	N
Range	<1.1V	<1.5V

Typical Characteristics

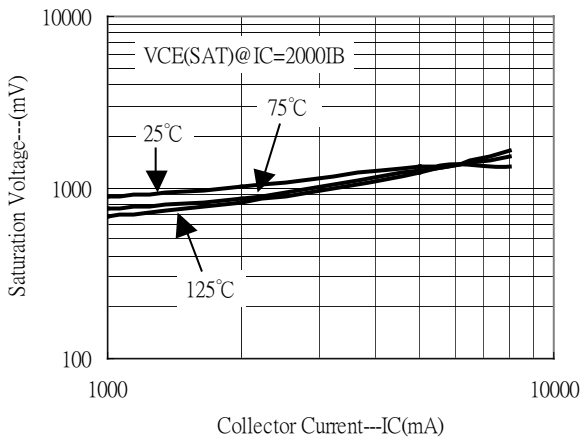
Current Gain vs Collector Current



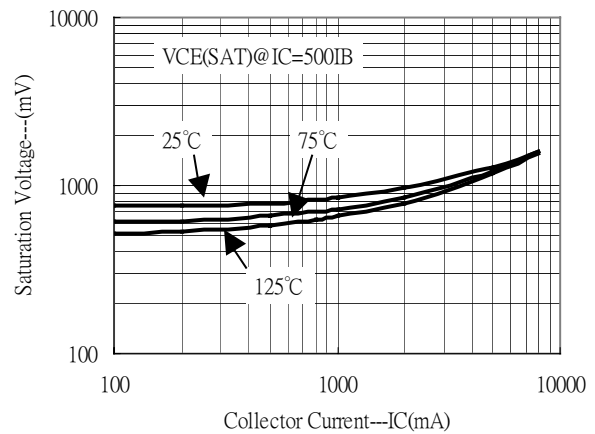
Saturation Voltage vs Collector Current



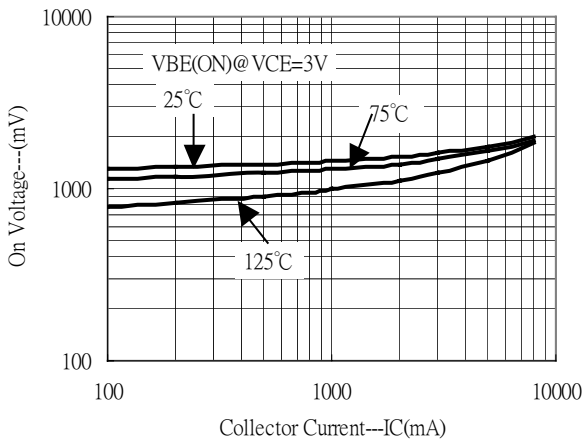
Saturation Voltage vs Collector Current



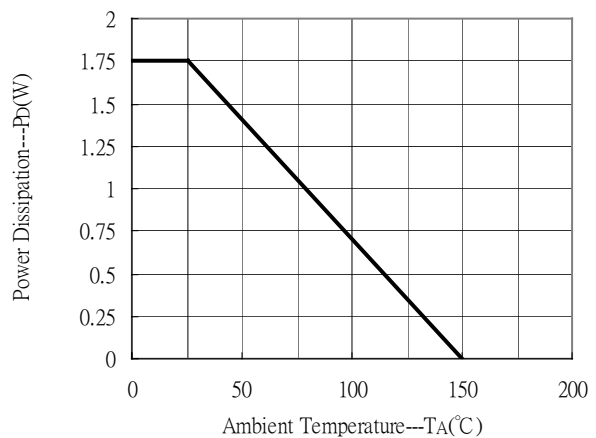
Saturation Voltage vs Collector Current



Saturation Voltage vs Collector Current

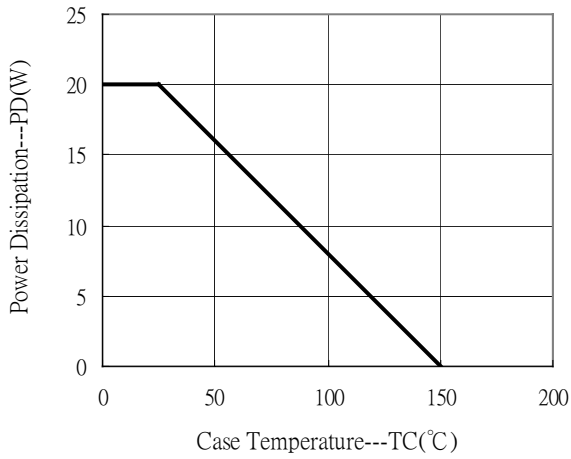


Power Derating Curve

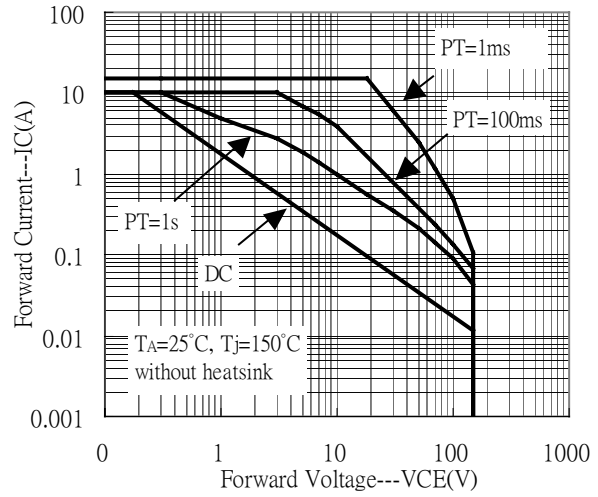


Typical Characteristics(Cont.)

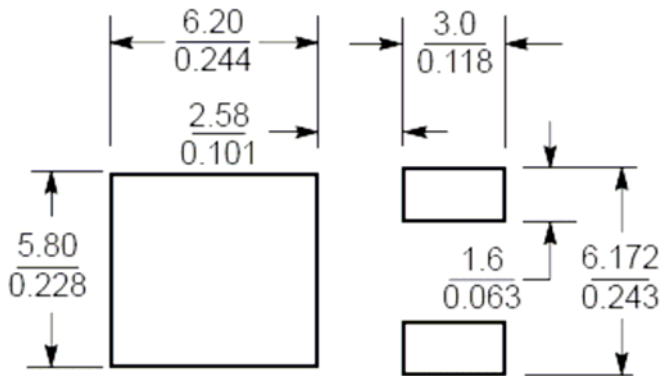
Power Derating Curve



Safe Operating Area

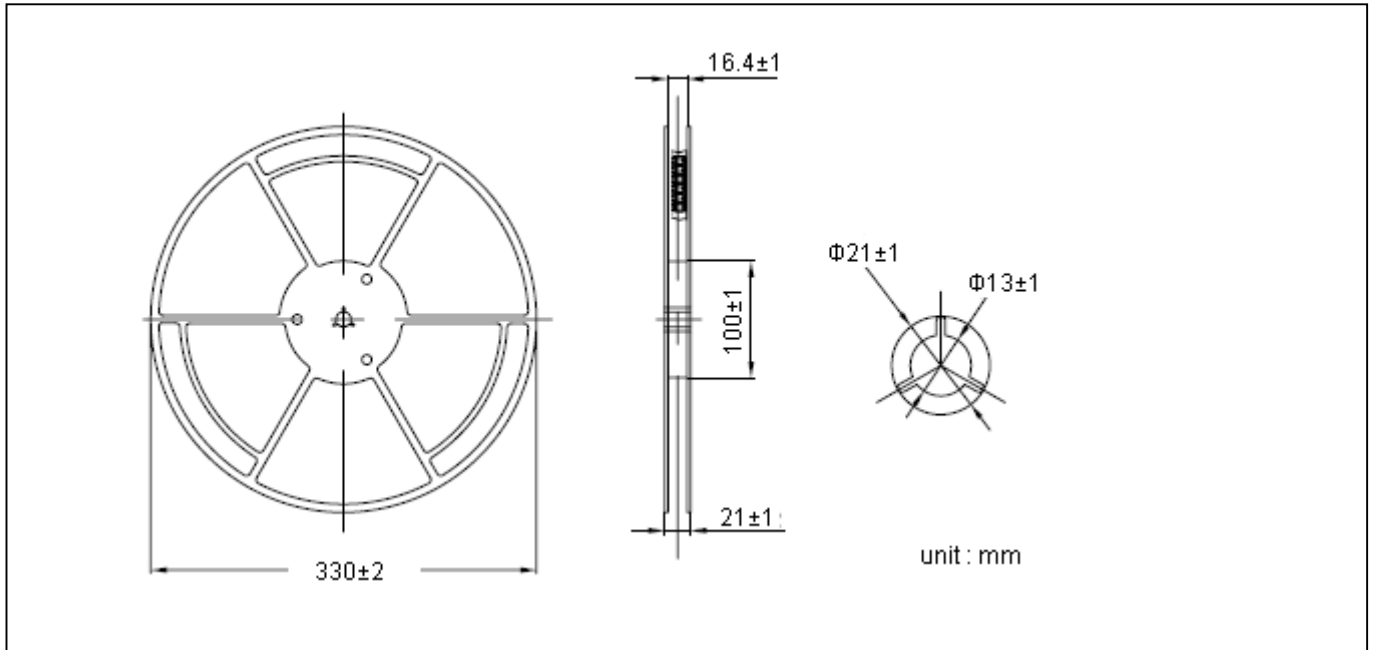


Recommended soldering footprint

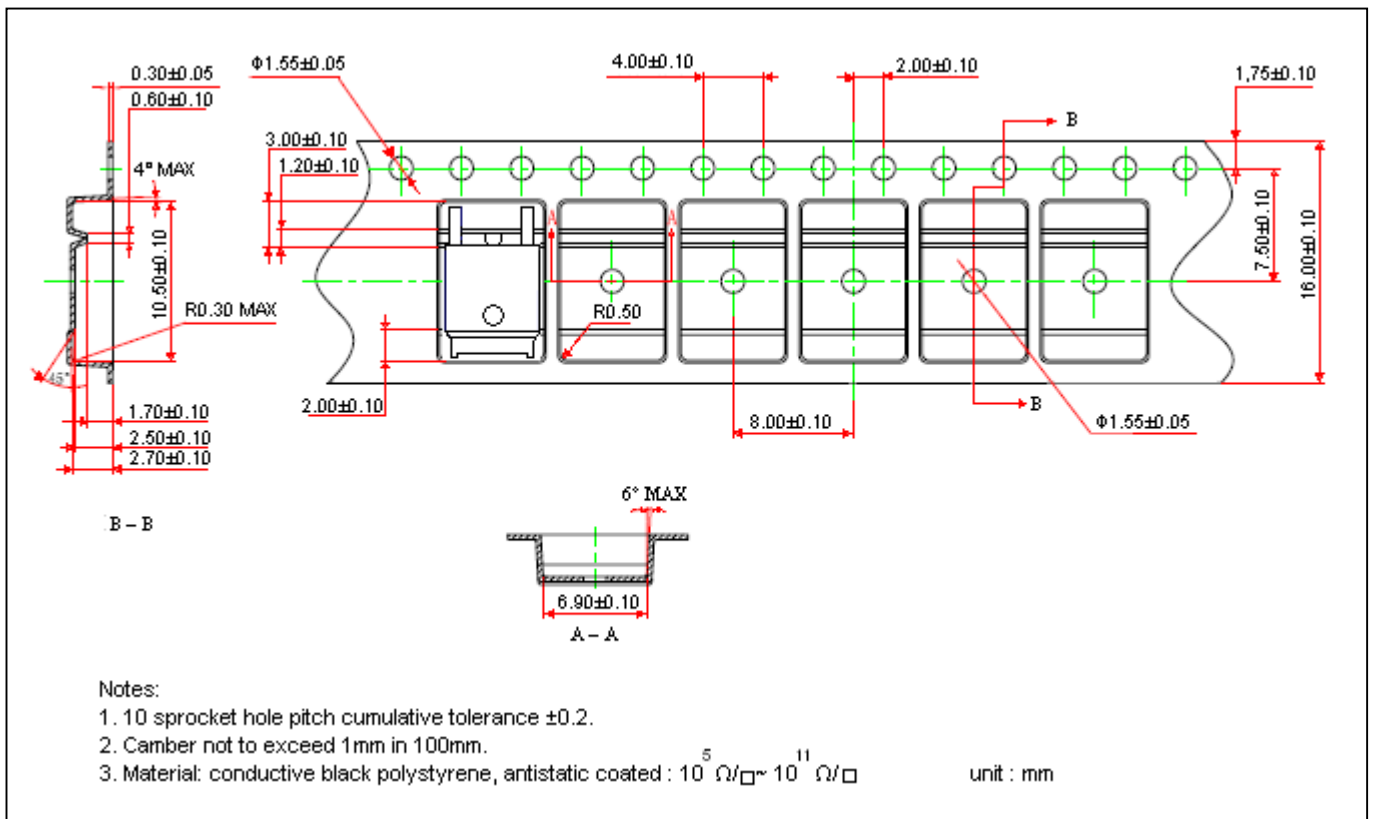


Unit ($\frac{\text{mm}}{\text{inch}}$)

Reel Dimension

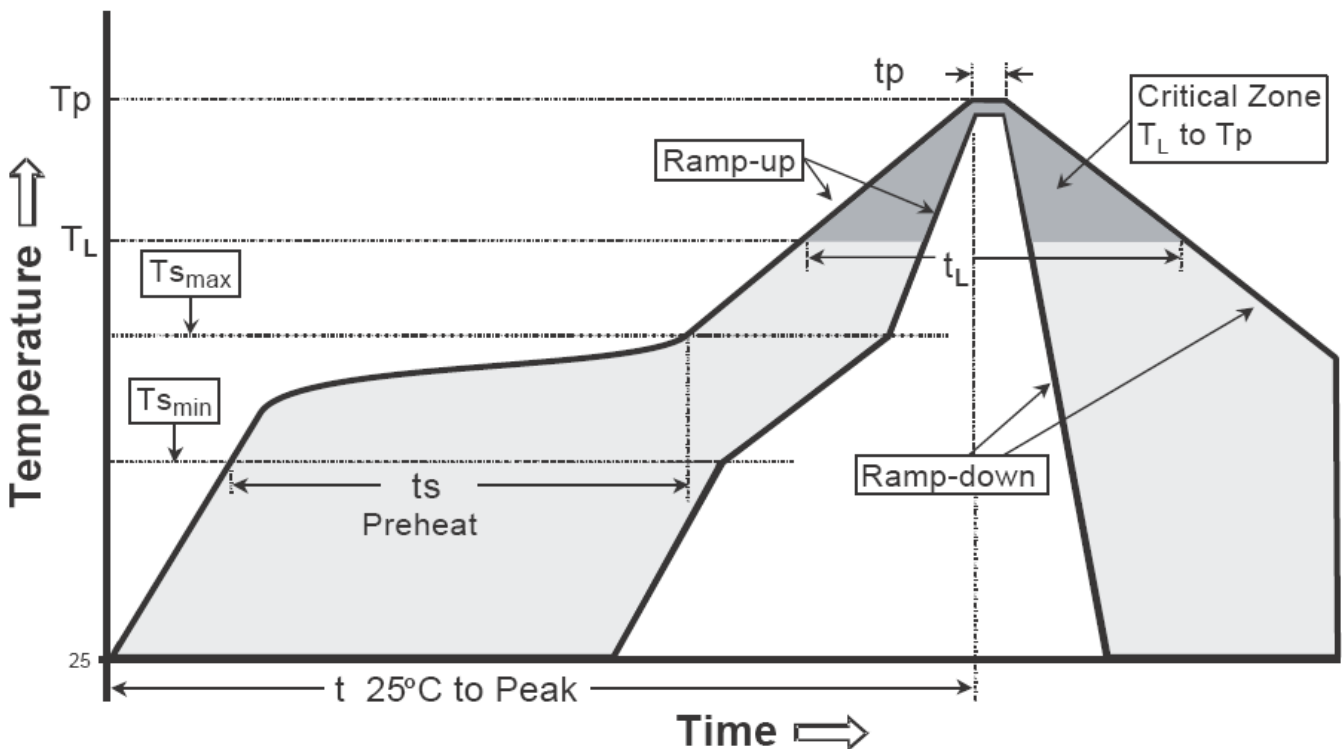


Carrier Tape Dimension



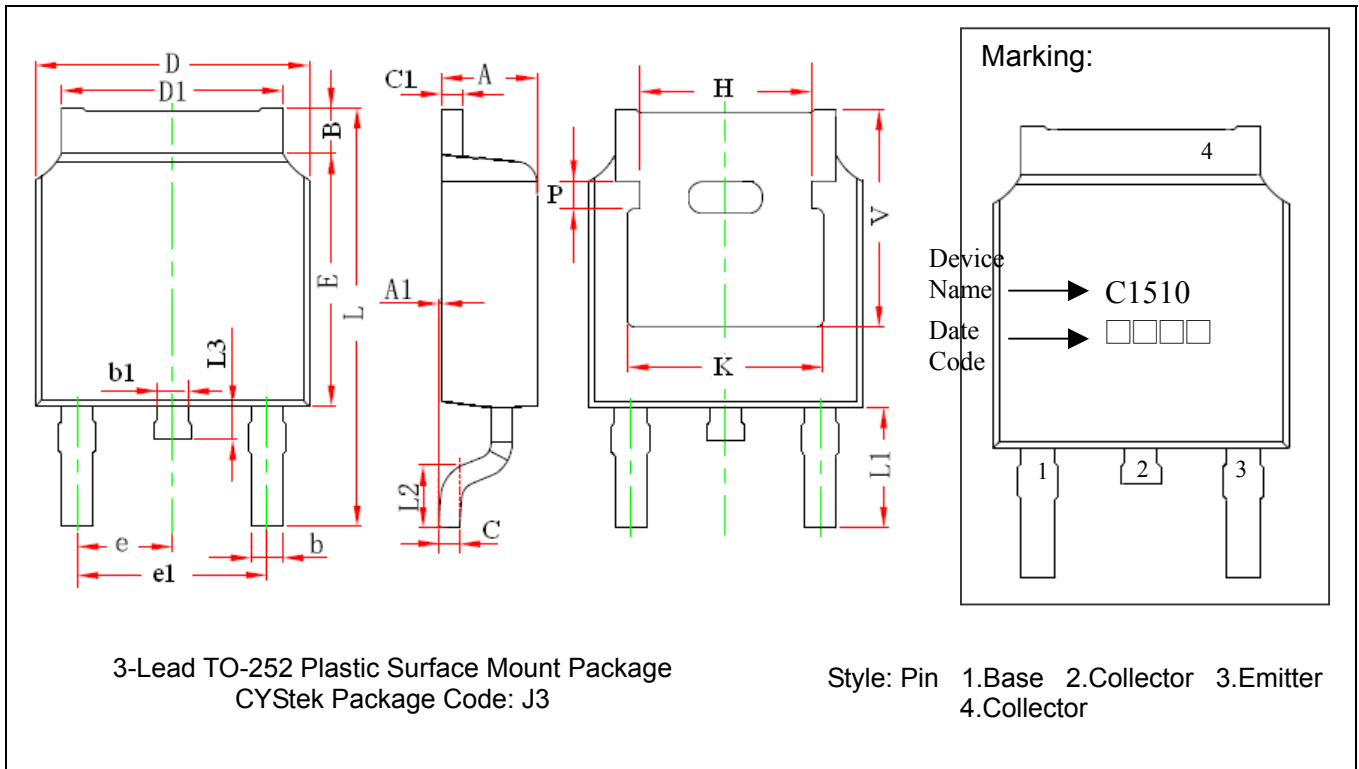
Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow


Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
Preheat		
-Temperature Min(T _{s min})	100°C	150°C
-Temperature Max(T _{s max})	150°C	200°C
-Time(t _{s min} to t _{s max})	60-120 seconds	60-180 seconds
Time maintained above:		
-Temperature (T _L)	183°C	217°C
- Time (t _L)	60-150 seconds	60-150 seconds
Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
Time within 5°C of actual peak temperature(t _p)	10-30 seconds	20-40 seconds
Ramp down rate	6°C/second max.	6°C/second max.
Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

TO-252 Dimension



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.087	0.094	2.200	2.400	e	0.086	0.094	2.186	2.386
A1	0.000	0.005	0.000	0.127	e1	0.172	0.188	4.372	4.772
B	0.039	0.048	0.990	1.210	H	0.163	REF	4.140	REF
b	0.026	0.034	0.660	0.860	K	0.190	REF	4.830	REF
b1	0.026	0.034	0.660	0.860	L	0.386	0.409	9.800	10.400
C	0.018	0.023	0.460	0.580	L1	0.114	REF	2.900	REF
C1	0.018	0.023	0.460	0.580	L2	0.055	0.067	1.400	1.700
D	0.256	0.264	6.500	6.700	L3	0.024	0.039	0.600	1.000
D1	0.201	0.215	5.100	5.460	P	0.026	REF	0.650	REF
E	0.236	0.244	6.000	6.200	V	0.211	REF	5.350	REF

Notes: 1.Controlling dimension: millimeters.
 2.Maximum lead thickness includes lead finish thickness, and minimum lead thickness is the minimum thickness of base material.
 3.If there is any question with packing specification or packing method, please contact your local CYStek sales office.

Material:

- Lead : Pure tin plated.
- Mold Compound: Epoxy resin family, flammability solid burning class: UL94V-0.

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